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TITLE: ORGANIC THIN FILM TRANSISTOR
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ABSTRACT:

PROBLEM TO BE SOLVED: To solve the problem of an organic thin film transistor technology employing a general purpose thin film process, e.g.

vacuum deposition, where a semiconductor film is deposited in polycrystalline state that a sufficiently high mobility cannot be attained due to energy barrier in the grain boundary and thereby a sufficiently high source-drain current cannot be attained.

SOLUTION: In order to introduce another substance for reducing the energy barrier into the grain boundary part of an organic semiconductor thin film, an organic compound 20 having a polarity opposite to that of an organic semiconductor layer 50 is attached to the semiconductor layer 50 on the side

opposite to an insulation layer 60.

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